

Complementary Dual General Purpose Amplifier Transistor

HN1B01FDW1T1G, SHN1B01FDW1T1G

PNP and NPN Surface Mount

Features

- High Voltage and High Current: $V_{CEO} = 50\text{ V}$, $I_C = 200\text{ mA}$
- High h_{FE} : $h_{FE} = 200 \sim 400$
- Moisture Sensitivity Level: 1
- ESD Rating
 - ◆ Human Body Model: 3A
 - ◆ Machine Model: C
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{(BR)CBO}$	60	Vdc
Collector-Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter-Base Voltage	$V_{(BR)EBO}$	7.0	Vdc
Collector Current - Continuous	I_C	200	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

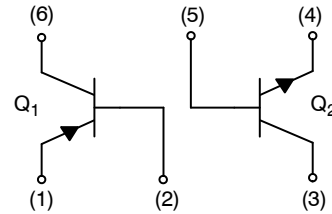
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation	P_D	380	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

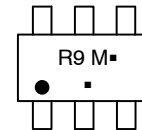
*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



SC-74
CASE 318F
STYLE 3



MARKING DIAGRAM



- R9 = Specific Device Code
- M = Date Code
- = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
HN1B01FDW1T1G	SC-74 (Pb-Free)	3,000/Tape & Reel
SHN1B01FDW1T1G	SC-74 (Pb-Free)	3,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

HN1B01FDW1T1G, SHN1B01FDW1T1G

Q1: PNP

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Breakdown Voltage ($I_C = 2.0\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	-50	-	Vdc
Collector–Base Breakdown Voltage ($I_C = 10\ \mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	-60	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\ \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	-7.0	-	Vdc
Collector–Base Cutoff Current ($V_{CB} = 45\text{ Vdc}$, $I_E = 0$)	I_{CBO}	-	-0.1	μAdc
Collector–Emitter Cutoff Current ($V_{CE} = 10\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$, $T_A = 80^\circ\text{C}$)	I_{CEO}	-	-0.1 -2.0 -1.0	μAdc μAdc mAdc
DC Current Gain (Note 1) ($V_{CE} = 6.0\text{ Vdc}$, $I_C = 2.0\text{ mAdc}$)	h_{FE}	-200	-400	-
Collector–Emitter Saturation Voltage ($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)	$V_{CE(sat)}$	-	-0.3	Vdc

Q2: NPN

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Breakdown Voltage ($I_C = 2.0\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	50	-	Vdc
Collector–Base Breakdown Voltage ($I_C = 10\ \mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	60	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\ \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	7.0	-	Vdc
Collector–Base Cutoff Current ($V_{CB} = 45\text{ Vdc}$, $I_E = 0$)	I_{CBO}	-	0.1	μAdc
Collector–Emitter Cutoff Current ($V_{CE} = 10\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$, $T_A = 80^\circ\text{C}$)	I_{CEO}	-	0.1 2.0 1.0	μAdc μAdc mAdc
DC Current Gain (Note 1) ($V_{CE} = 6.0\text{ Vdc}$, $I_C = 2.0\text{ mAdc}$)	h_{FE}	200	400	-
Collector–Emitter Saturation Voltage ($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)	$V_{CE(sat)}$	-	0.25	Vdc

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, D.C. $\leq 2\%$.

TYPICAL ELECTRICAL CHARACTERISTICS: PNP TRANSISTOR

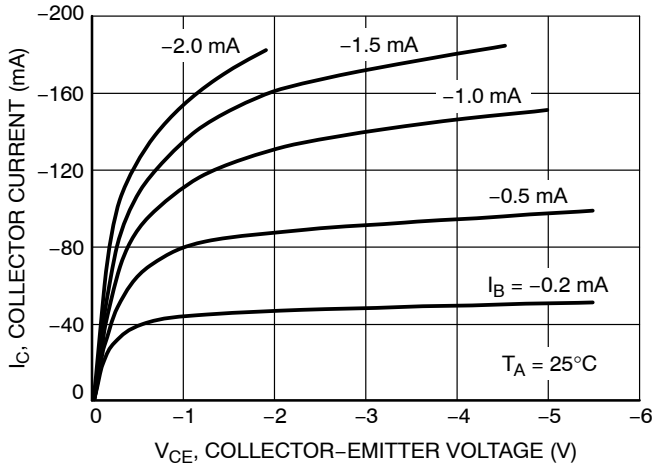


Figure 1. Collector Saturation Region

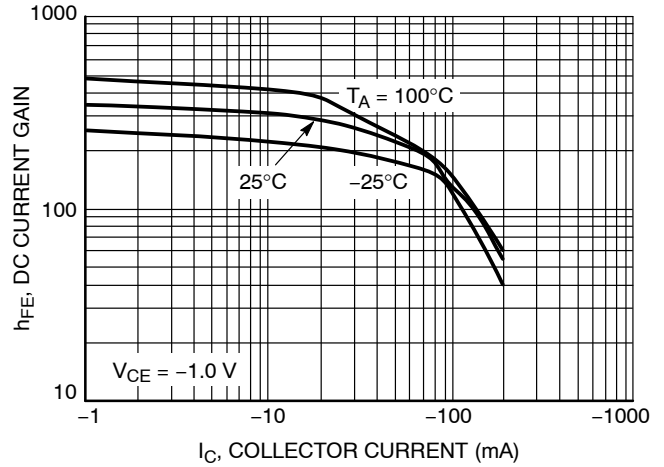


Figure 2. DC Current Gain

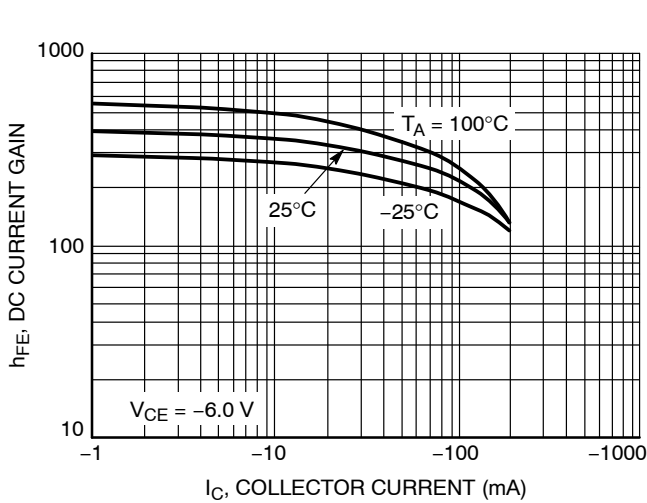


Figure 3. DC Current Gain

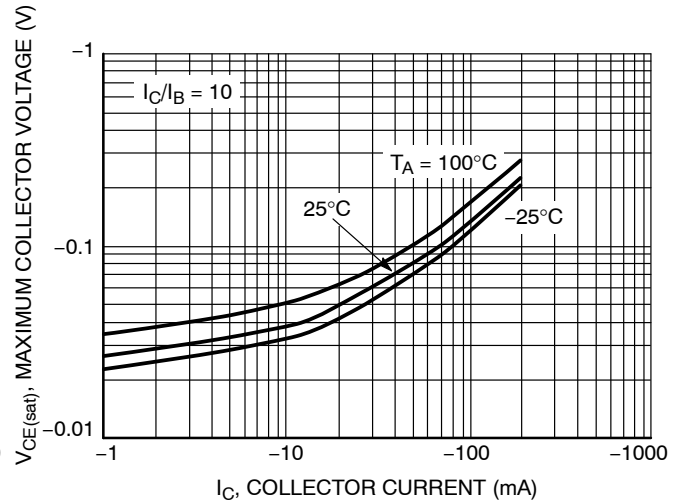


Figure 4. $V_{CE(sat)}$ versus I_C

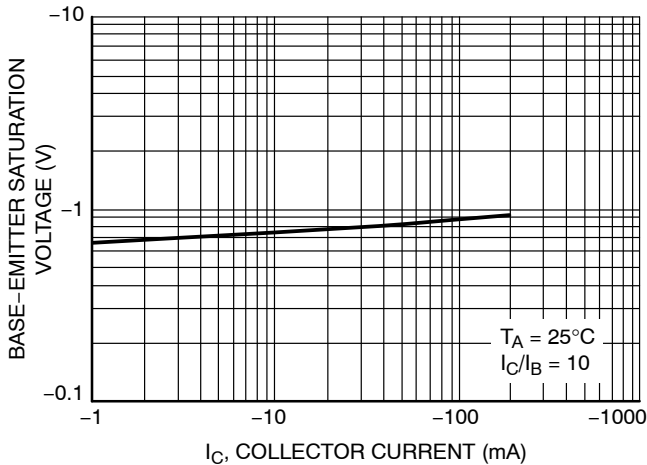


Figure 5. $V_{BE(sat)}$ versus I_C

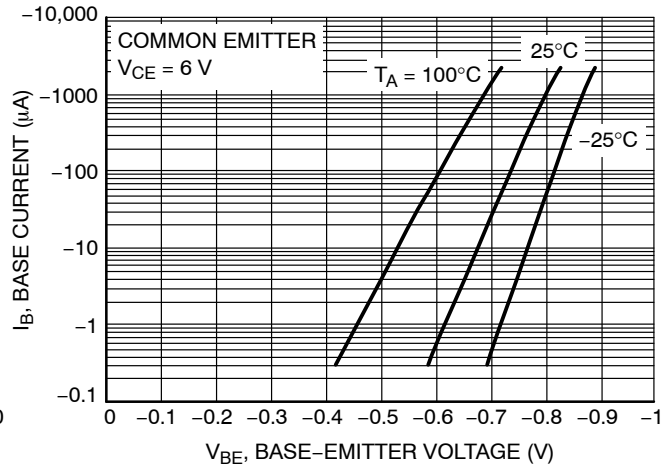


Figure 6. Base-Emitter Voltage

TYPICAL ELECTRICAL CHARACTERISTICS: NPN TRANSISTOR

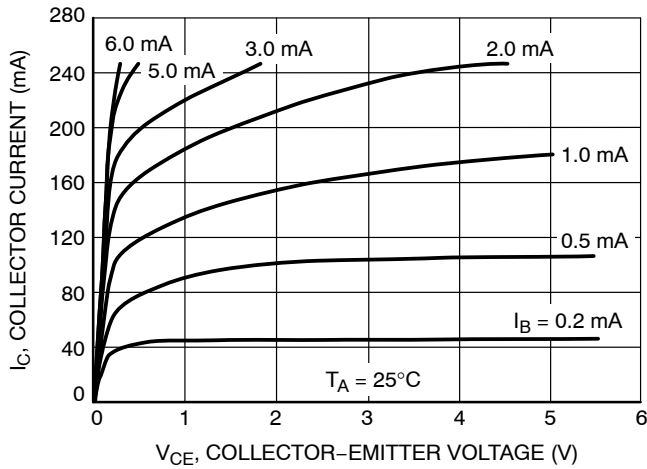


Figure 7. Collector Saturation Voltage

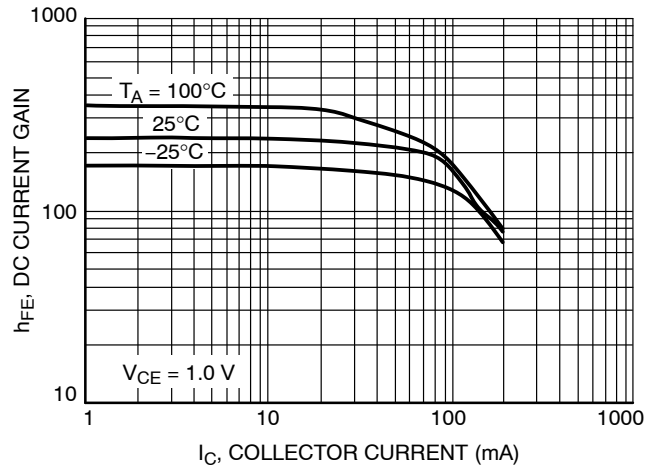


Figure 8. DC Current Gain

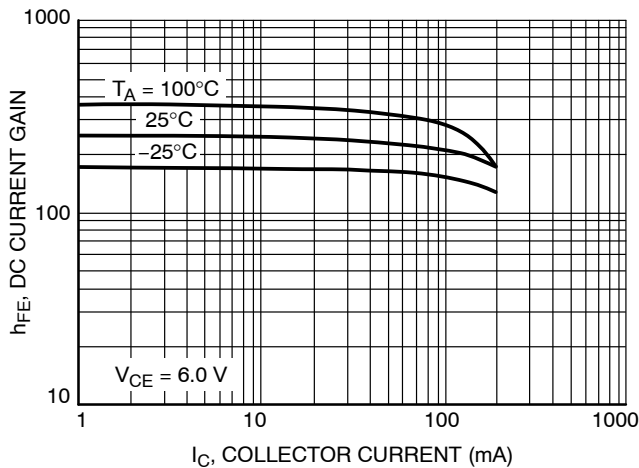


Figure 9. DC Current Gain

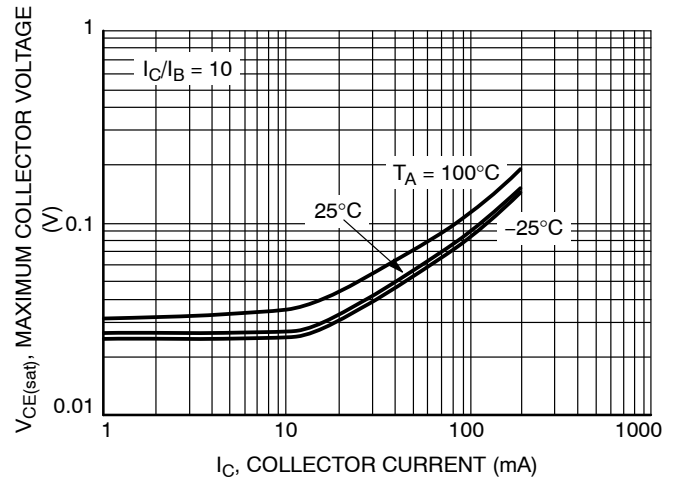


Figure 10. $V_{CE(sat)}$ versus I_C

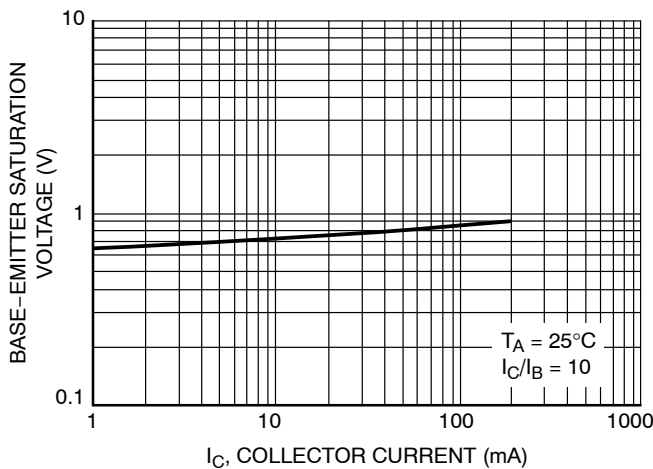


Figure 11. $V_{BE(sat)}$ versus I_C

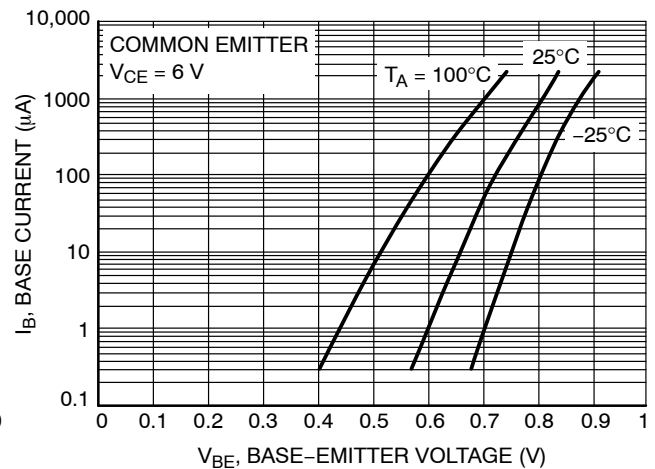


Figure 12. Base-Emitter Voltage

HN1B01FDW1T1G, SHN1B01FDW1T1G

TYPICAL ELECTRICAL CHARACTERISTICS

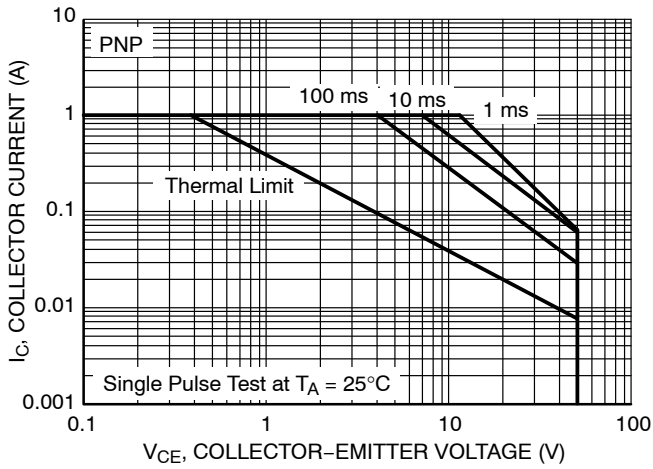


Figure 13. PNP Safe Operating Area

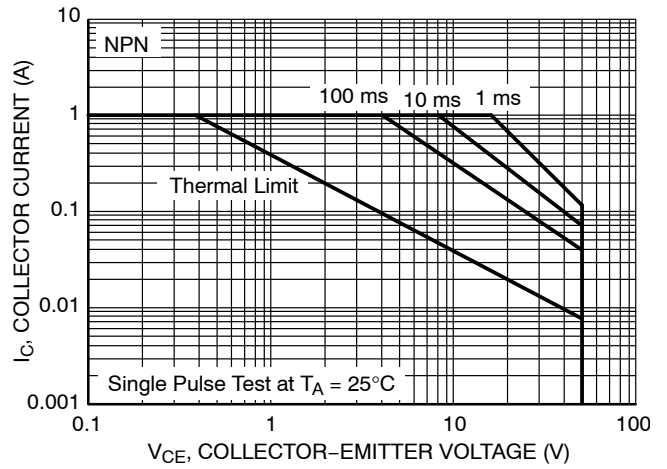


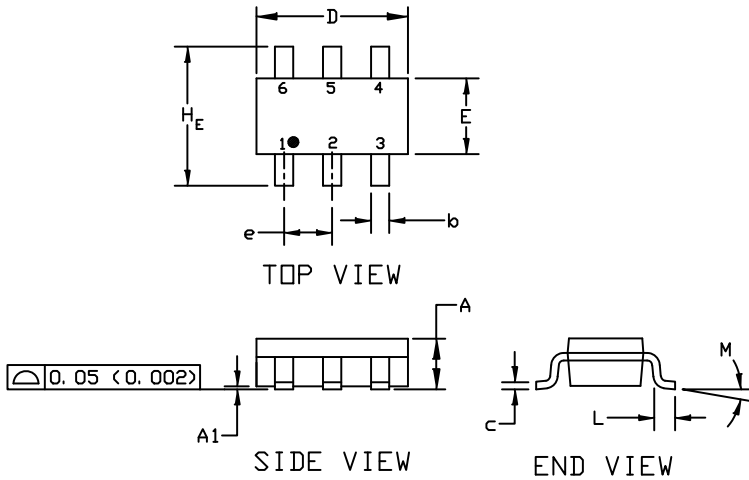
Figure 14. NPN Safe Operating Area



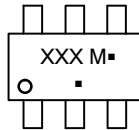
SCALE 2:1

SC-74
CASE 318F
ISSUE P

DATE 07 OCT 2021



GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

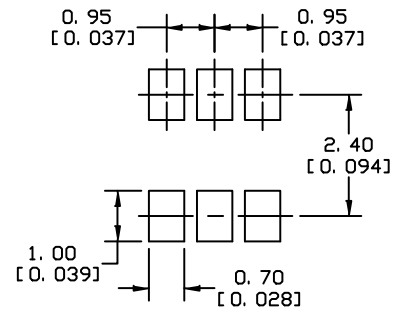
(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
2. CONTROLLING DIMENSION: INCHES
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
H _E	2.50	2.75	3.00	0.099	0.108	0.118
L	0.20	0.40	0.60	0.008	0.016	0.024
M	0°	---	10°	0°	---	10°



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

SOLDERING FOOTPRINT

- | | | | | | |
|---|--|---|--|---|---|
| <p>STYLE 1:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE</p> | <p>STYLE 2:
PIN 1. NO CONNECTION
2. COLLECTOR
3. EMITTER
4. NO CONNECTION
5. COLLECTOR
6. BASE</p> | <p>STYLE 3:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1</p> | <p>STYLE 4:
PIN 1. COLLECTOR 2
2. EMITTER 1/EMITTER 2
3. COLLECTOR 1
4. EMITTER 3
5. BASE 1/BASE 2/COLLECTOR 3
6. BASE 3</p> | <p>STYLE 5:
PIN 1. CHANNEL 1
2. ANODE
3. CHANNEL 2
4. CHANNEL 3
5. CATHODE
6. CHANNEL 4</p> | <p>STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE</p> |
| <p>STYLE 7:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1</p> | <p>STYLE 8:
PIN 1. EMITTER 1
2. BASE 2
3. COLLECTOR 2
4. EMITTER 2
5. BASE 1
6. COLLECTOR 1</p> | <p>STYLE 9:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2</p> | <p>STYLE 10:
PIN 1. ANODE/CATHODE
2. BASE
3. EMITTER
4. COLLECTOR
5. ANODE
6. CATHODE</p> | <p>STYLE 11:
PIN 1. EMITTER
2. BASE
3. ANODE/CATHODE
4. ANODE
5. CATHODE
6. COLLECTOR</p> | |

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